

Title (en)
METHODS FOR SILICON OXIDE AND OXYNITRIDE DEPOSITION USING SINGLE WAFER LOW PRESSURE CVD

Title (de)
VERFAHREN ZUR ABSCHIEDUNG VON SILICIUMOXID UND SILICIUMOXIDNITRID MITTELS EINZELWAFER-NIEDERDRUCK-CVD

Title (fr)
PROCEDES DE DEPOT DE DIOXYDE DE SILICIUM ET D'OXYNITRIDE UTILISANT UN PROCEDE DCPV A FAIBLE PRESSION A UNE SEULE TRANCHE

Publication
EP 1470264 A1 20041027 (EN)

Application
EP 02795980 A 20021219

Priority
• US 0240867 W 20021219
• US 4102601 A 20011228

Abstract (en)
[origin: WO03057942A1] An oxide and an oxynitride films and their methods of fabrication are described. The oxide or the oxynitride film is grown on a substrate that is placed in a deposition chamber. A silicon source gas (or a silicon source gas with a nitridation source gas) and an oxidation source gas are decomposed in the deposition chamber using a thermal energy source. A silicon oxide (or an oxynitride) film is formed above the substrate wherein total pressure for the deposition chamber is maintained in the range of 50 Torr to 350 Torr and wherein a flow ratio for the silicon source gas (or the silicon source gas with the nitridation source gas) and the oxidation source gas is in the range of 1:50 to 1:10000 during a deposition process.
[origin: WO03057942A1] An oxide and an oxynitride films and their methods of fabrication are described. The oxide or the oxynitride film is grown on a substrate that is placed in a deposition chamber. A silicon source gas or a silicon source gas with a nitridation source gas and an oxidation source gas are decomposed in the deposition chamber using a thermal energy source. A silicon oxide or an oxynitride film is formed above the substrate wherein total pressure for the deposition chamber is maintained in the range of 50 Torr to 350 Torr and wherein a flow ratio for the silicon source gas or the silicon source gas with the nitridation source gas and the oxidation source gas is in the range of 1:50 to 1:10000 during a deposition process.

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